
RC900

MEM452 8M Memory module

Hardware reference manual

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RC Computer

Keywords:

MEM452, RC900 Memory Module

Abstract:

This paper contains a hardware description of the MEM452 memory module. The MEM452 provides 2 Megabytes of system memory for the RC900 series.

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1. GENERAL INFORMATION

1.1 Introduction

The MEM452 is a 8 Mega byte memory module intended for use in the RC900 series.

The memory is organized in two banks each containing 1024 K words 32 bits wide plus 4 parity bits.

The two banks share data and address lines but have separate control lines (RAS, CAS and WE).

The address- and control- lines are buffered to groups of memory chips, whereas the databus connects the memory chips directly with the plug.

This manual describes the MEM452 board in three major sections. The first section gives a short description and specification of the board. The second section contains a functional description. The third section is devoted to the detailed hardware description with circuit- logic- and timing-diagrams.

1.2 Specifications

1.2.1 Performance specifications

capacity	:	8388608 bytes of 9 bit (8 + parity)
organisation	:	2 banks of 1048576 words
word length	:	32 bits + 4 parity bits
page size	:	4096 bytes
access time	:	read from idle bank : 110 nsec.
	:	read from selected page
		page hit : 60 nsec.
		page miss : 205 nsec.
cycle time	:	page hit : 120 nsec.
		page miss : 220 nsec.
capacity	:	32 Kbytes.
wordlength	:	16 bits.
access time	:	Depends on the programmed System bus speed.

1.2.2 Environmental Specifications

Operating temperature	:	0 to 40 degrees C.
Relative Humidity	:	20% to 80% (non condensing).
Altitude	:	0 to 6,000 feet.

1.2.3 Physical Specification

Width	:	142 mm
Length	:	213 mm
Hight	:	14 mm
Weight	:	350 gram

The dimensions are excluding the mounting.

1.2.4 Power Specification

Power consumption

Dissipation	:	2.5 W max.
Vcc	:	+5V +/- 5% (2.5A max.)

2 FUNCTIONAL DESCRIPTION

2.1 DRAM operation

The memory is equipped with 72 chips 1M by 1 bit Dynamic Random Access Memory.

The 1048576 bits are stored in 1048576 small capacitors each charged to a high or a low voltage representing the bit value. With each capacitor is attached a transistor being the gate to the charge. The transistor-capacitor pairs are organized in 1024 rows with 1024 pairs in each. All transistors in a row are turned on and off at the same time gating the charge of each capacitor to one of 1024 bus lines transferring the charges to an array of 1024 amplifier/latches constituting the row register. These bus lines with the associated amplifier/latch are called coloums. Access to one of the 1024 coloums from the singlebit input and output on the chip is done via a 1024/1 multiplexer.

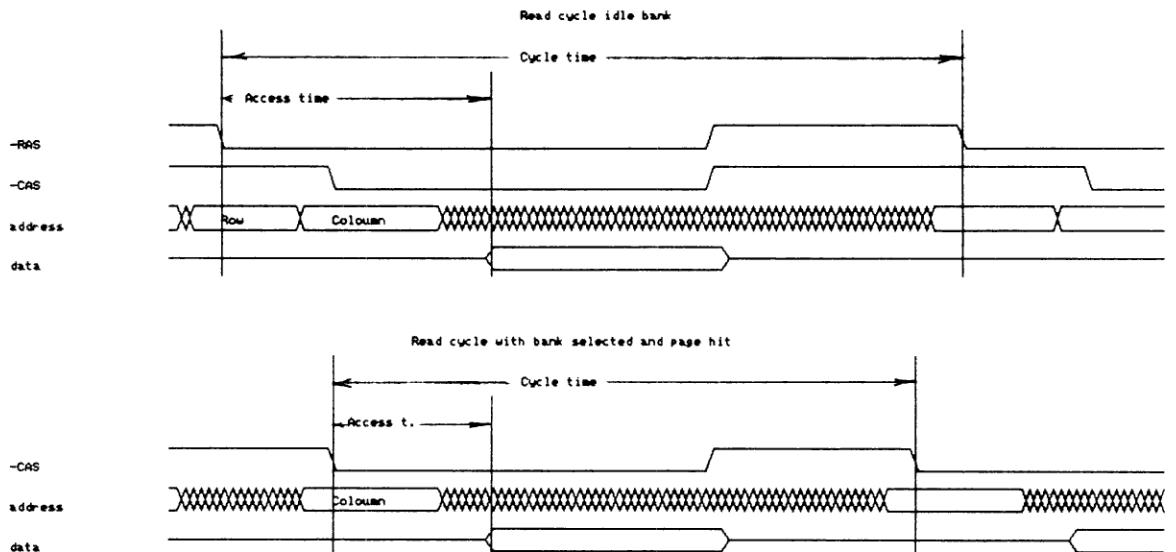


fig. 1 DRAM timing

The memory chip is controlled with three signals: RAS (Row Address Select), CAS (Column Address Select) and WE (Write Enable). The 18 bit address is multiplexed into the chip in two portions of 9 bits each. An access to a bit starts with applying the 9 most significant address bits to the address bus and activate RAS. This will latch the row address into a row address register and select the corresponding row and load it into the row register. Next step is to shift the remaining 9 address bits onto the address bus and activate CAS. This controls the column multiplexer to select one bit in the row register to be gated to the output or to be modified according to the data input (if WE is active). As long time RAS is kept active it is possible to access bits in the row register only specifying the column address, WE and reactivating CAS. When RAS is deactivated, the current contents of the row register (modified or unmodified) is stored back into the row capacitors (this is referred to in the databooks as the precharge time), then the row is "closed", and when CAS is released as well the chip is deselected. The capacitors being not totally "tight" require refresh evry 4 millisecond. This is done for a row each time it is accessed. Row access without bit access (without CAS being activated) are called refresh cycles.

3. TECHNICAL DESCRIPTION

3.1 Introduction

This section gives the detailed description of the MEM452 circuit board until the chip level. For the technical description of the used chips please refer to the manufacturer manuals in the appendices.

3.2 Block diagram

Figure 2 shows a detailed block diagram of the MEM452 intended to provide an overview of the board. The blocks correspond to physical and/or logical entities and are labeled with numbers referring to the logic diagrams in section 3.3, where the exact electrical connections are drawn. Two or more numbers separated with commas indicate that the block is spread over more diagrams.

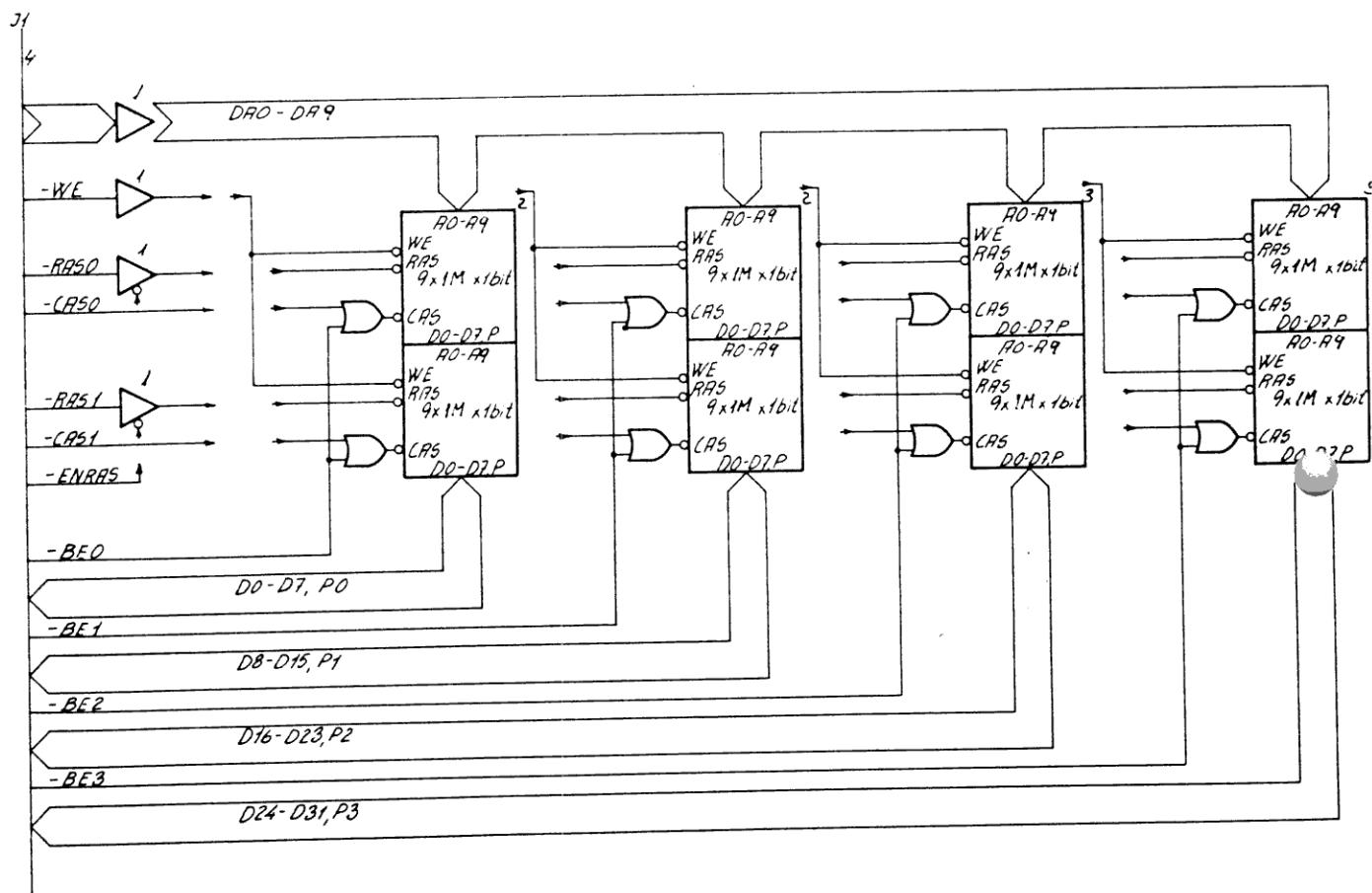


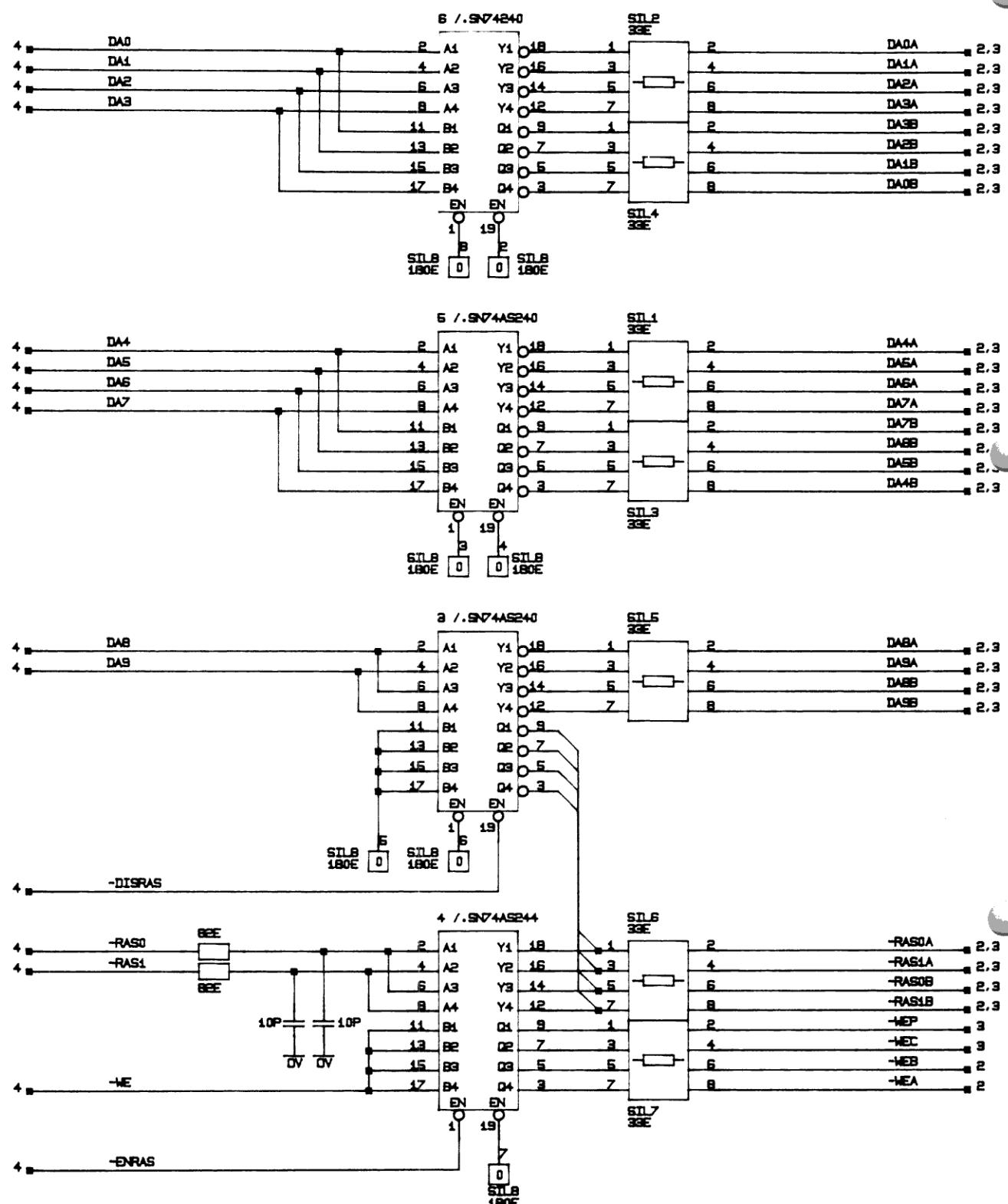
Fig. 2 detailed block diagram.

3.3 Logic diagrams

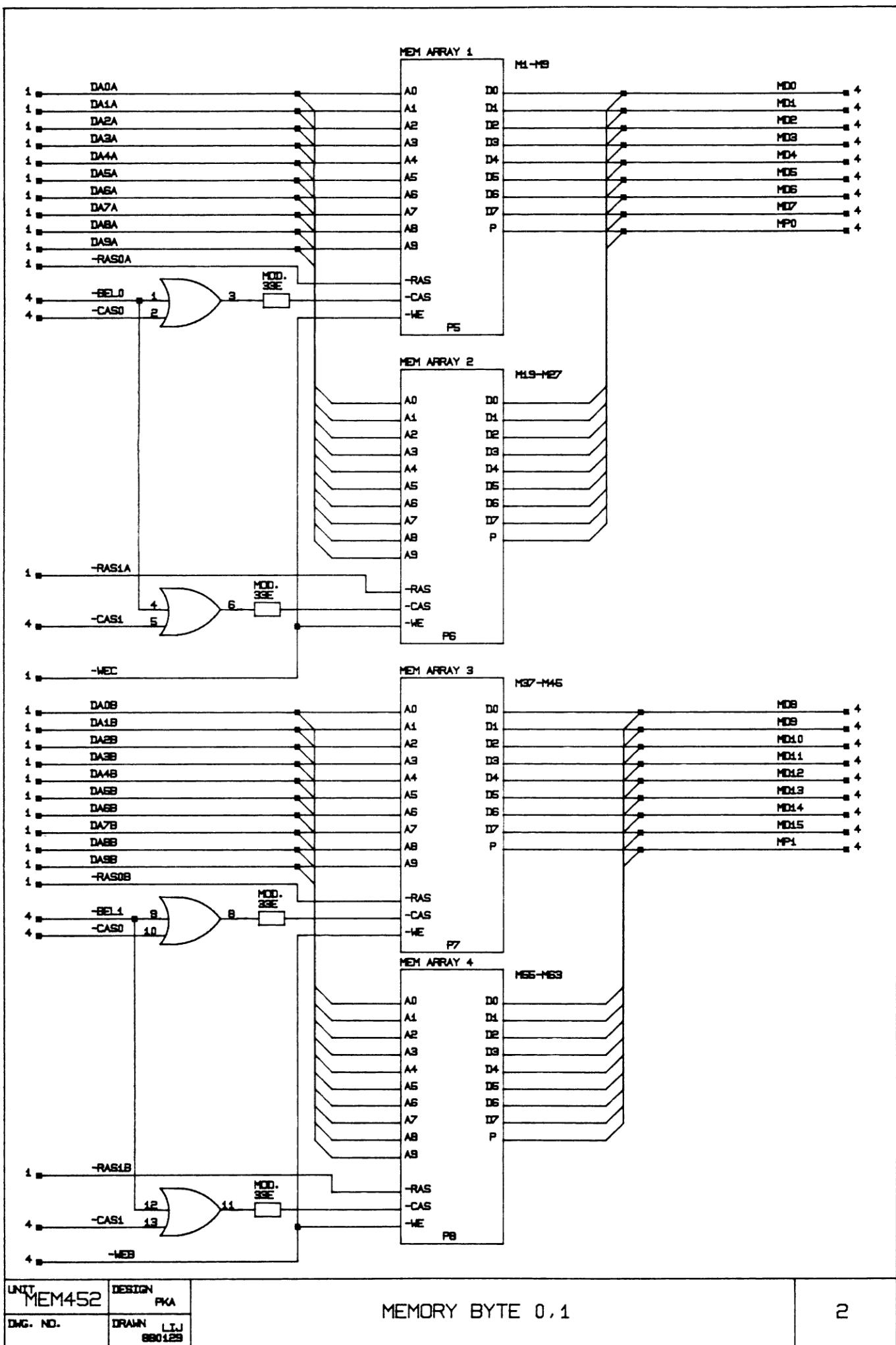
This section contains the logic diagrams of the MEM452.

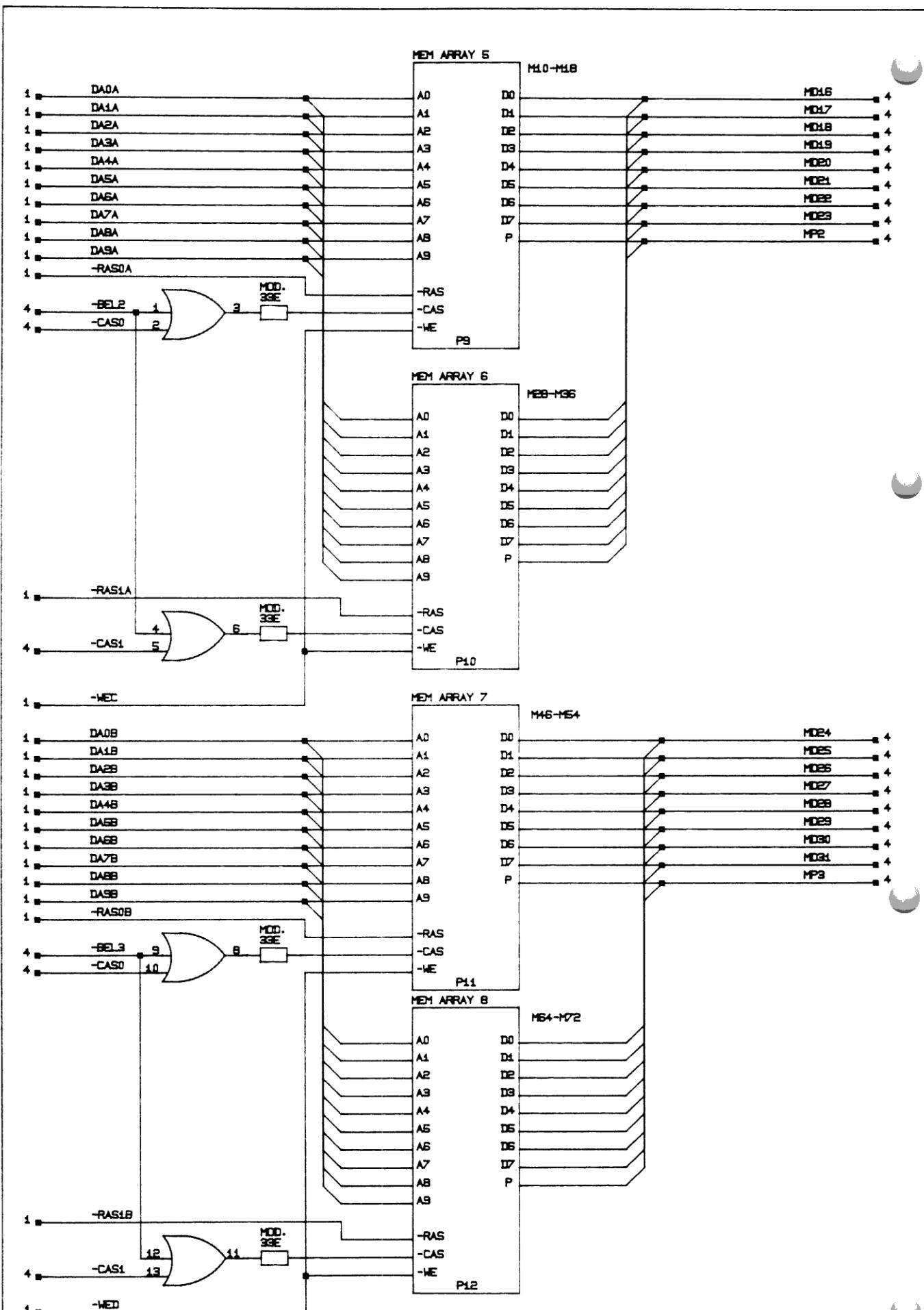
The pages of the diagram are numbered separately from the pagination of the manual. These diagram numbers are used on the diagrams for source and destination references, where signals enter or leave a page.

The position code found above each component on the diagrams corresponds to the position number marked on the printed circuit board.



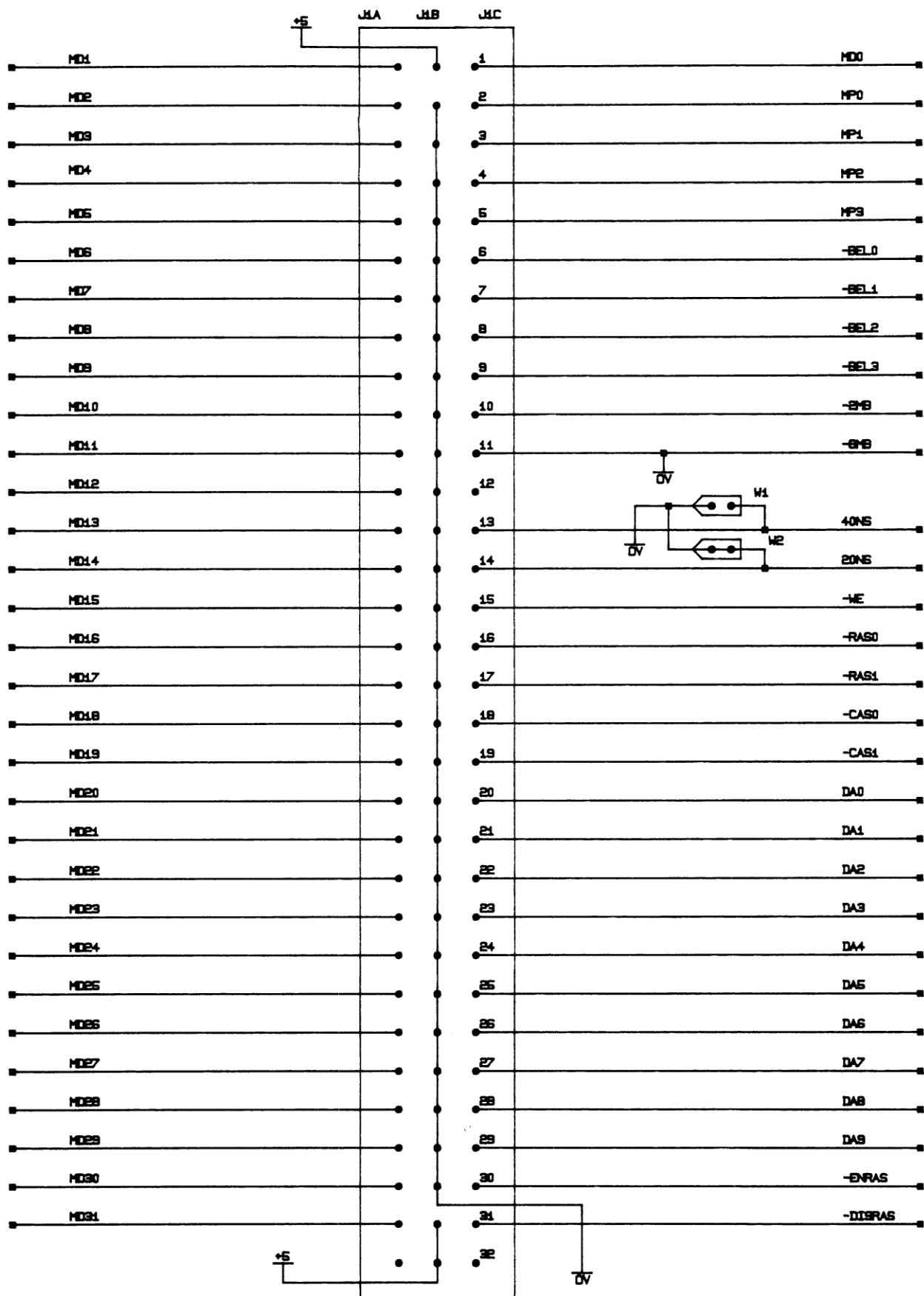
UNIT MEM452	DESIGN PKA	BUFFERE	1
DRW. NO.	DRAWN LIJ 880129		



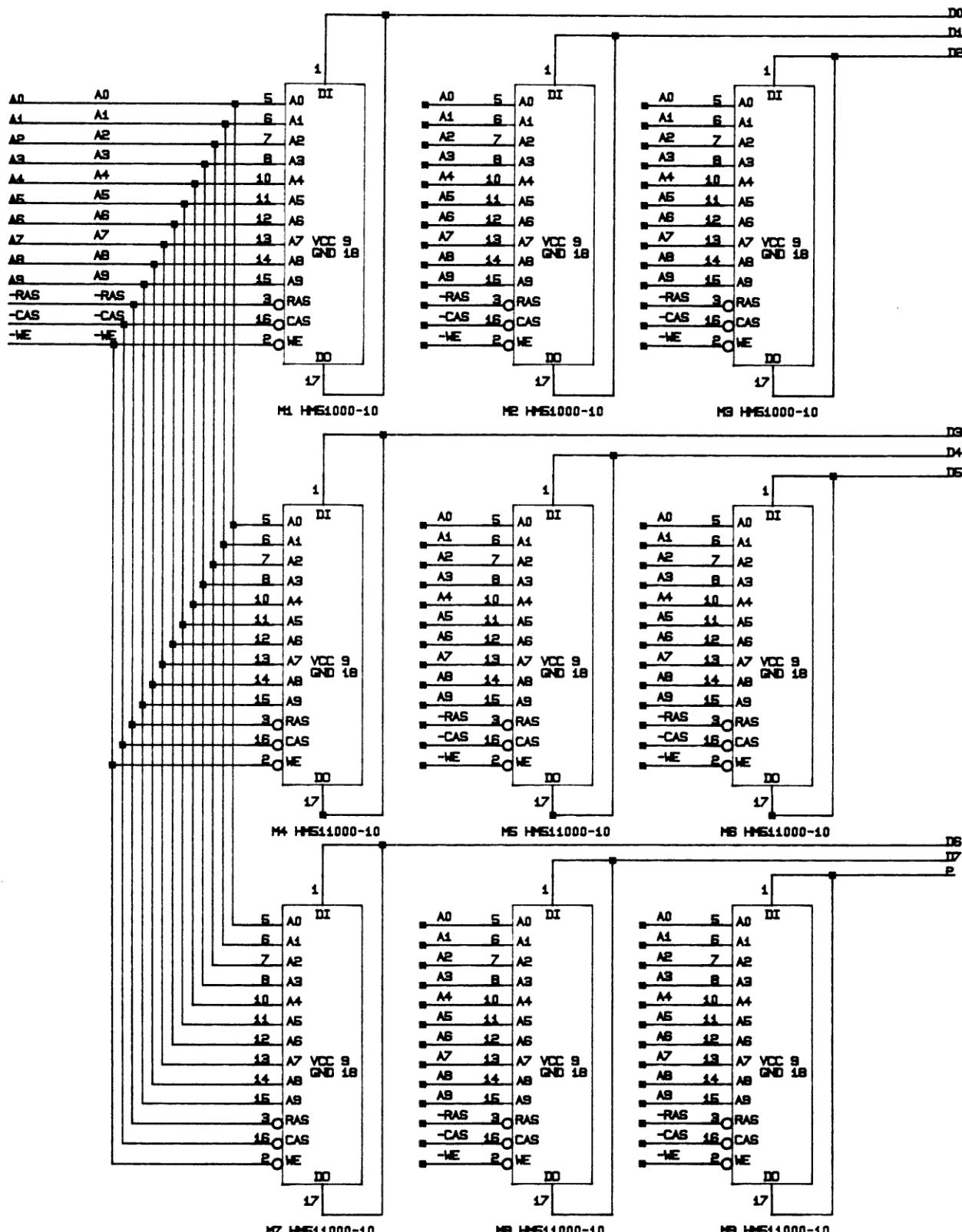


UNIT MEM452	DESIGN PKA	
DRW. NO.	DRAWN LJL 880129	

MEMORY BYTE 2,3



UNIT MEM452	DESIGN PKA	CONNECTOR	4
ENG. NO.	DRAWN LJ 880129		



UNIT MEM452	DESIGN PKA	
DRG. NO.	DRAWN L.I.J. 980129	

1M*9 BIT MEM ARRAY

3.4 Assembly drawing

